

Abstracts

X-Band Burnout Characteristics of GaAs MESFETs (1982 [MWSYM])

J.J. Whalen and R.T. Kemerley. "X-Band Burnout Characteristics of GaAs MESFETs (1982 [MWSYM])." 1982 MTT-S International Microwave Symposium Digest 82. 1 (1982 [MWSYM]): 286-288.

X-Band microsecond pulse, millisecond pulse, and CW burnout data have been measured for GaAs MESFETs. Values of incident pulse power required to cause burn-out are presented and discussed.

 [Return to main document.](#)

Click on title for a complete paper.